



B5818W SCHOTTKY BARRIER DIODE

FEATURES

Power dissipation

$$P_D: 450 \text{ mW (} T_{amb}=25^\circ\text{C)}$$

Collector current

$$I_F: 1 \text{ A}$$

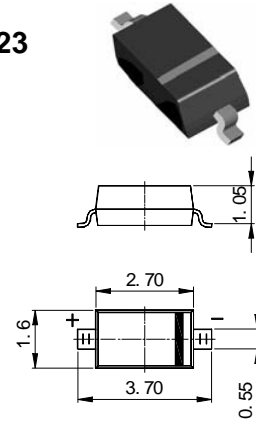
Collector-base voltage

$$V_R: 30 \text{ V}$$

Operating and storage junction temperature range

$$T_J, T_{stg}: -55^\circ\text{C to } +150^\circ\text{C}$$

SOD-123



Unit: mm

MARKING: SK

ELECTRICAL CHARACTERISTICS ($T_{amb}=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Reverse breakdown voltage	$V_{(BR)}$	$I_R=1\text{mA}$	30		V
Reverse voltage leakage current	I_R	$V_R=20\text{V}$		1	mA
Forward voltage	V_F	$I_F=1\text{A}$ $I_F=3\text{A}$		0.55 0.875	V
Diode capacitance	C_D	$V_R=4\text{V}$, $f=1\text{MHz}$		110	pF